

HAT1038R/HAT1038RJ

Silicon P Channel Power MOS FET
High Speed Power Switching

HITACHI

ADE-208-663C (Z)

4th. Edition

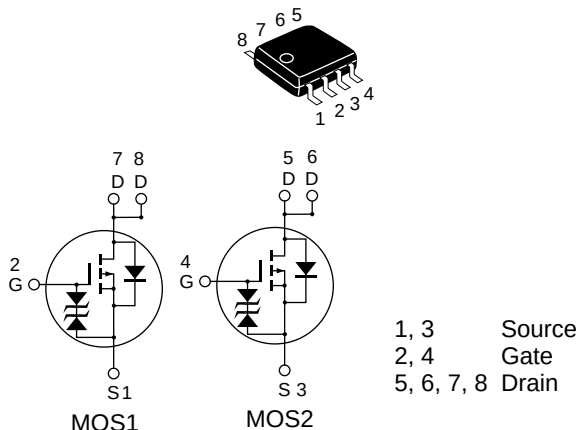
February 1999

Features

- For Automotive Application (at Type Code “J “)
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline

SOP-8



Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage		V_{DSS}	− 60	V
Gate to source voltage		V_{GSS}	± 20	V
Drain current		I_D	− 3.5	A
Drain peak current		$I_{D(pulse)}$ ^{Note1}	− 28	A
Body-drain diode reverse drain current		I_{DR}	− 3.5	A
Avalanche current	HAT1038R	I_{AP} ^{Note4}	—	—
	HAT1038RJ		− 3.5	A
Avalanche energy	HAT1038R	E_{AR} ^{Note4}	—	—
	HAT1038RJ		1.05	mJ
Channel dissipation		P_{ch} ^{Note2}	2	W
Channel dissipation		P_{ch} ^{Note3}	3	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	− 55 to + 150	°C

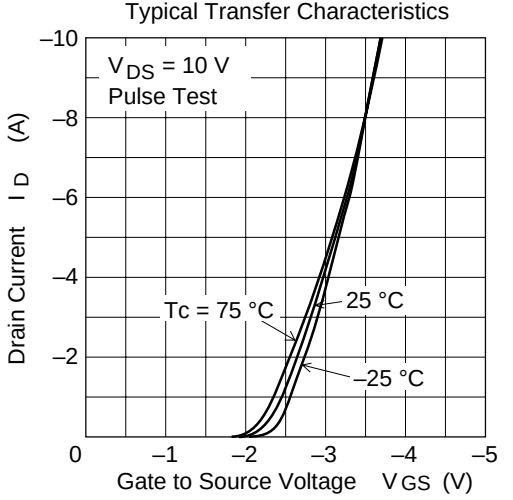
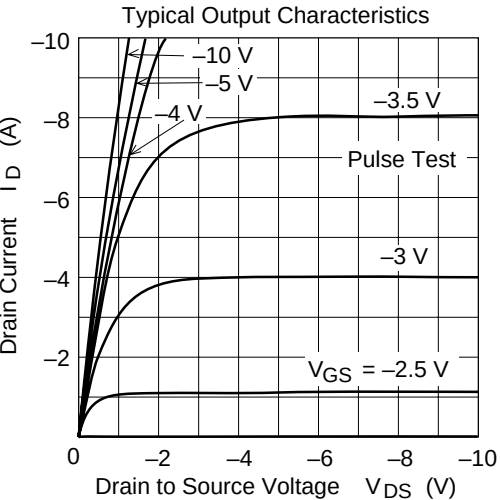
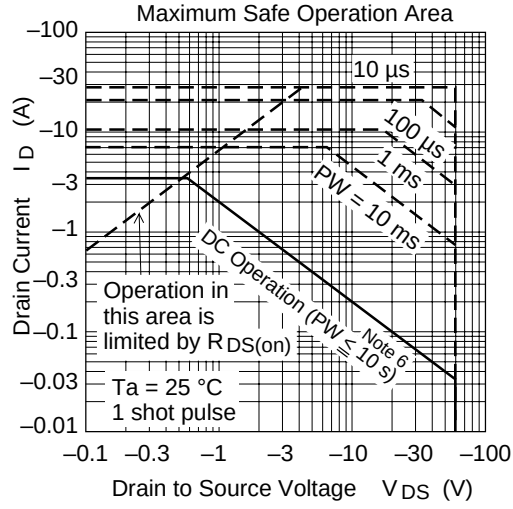
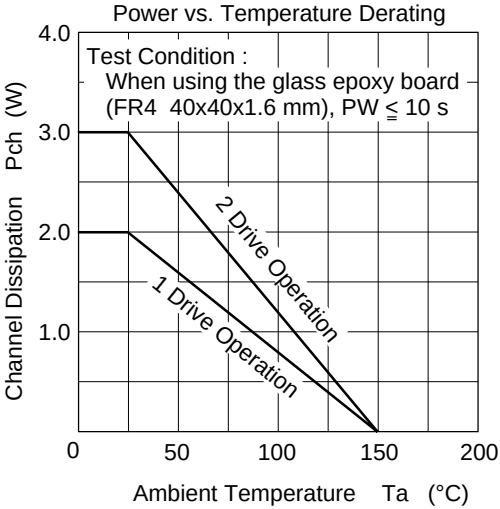
- Note:
- 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 - 2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10 s$
 - 3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10 s$
 - 4. Value at $T_{ch} = 25^{\circ}C$, $R_g \geq 50 \Omega$

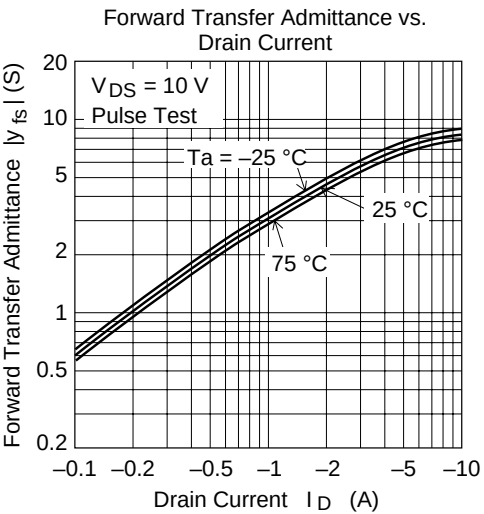
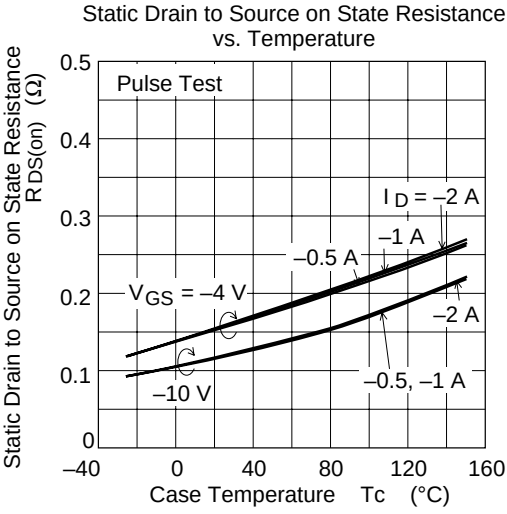
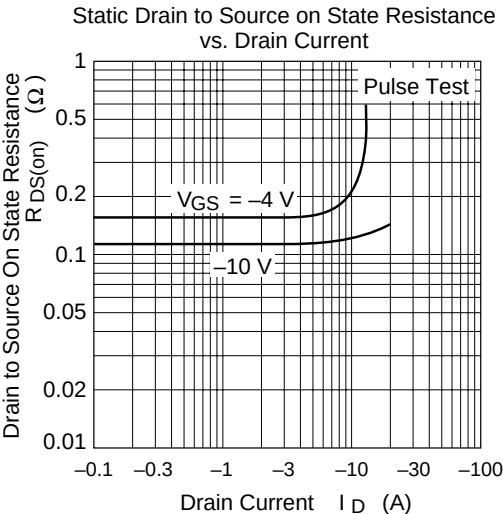
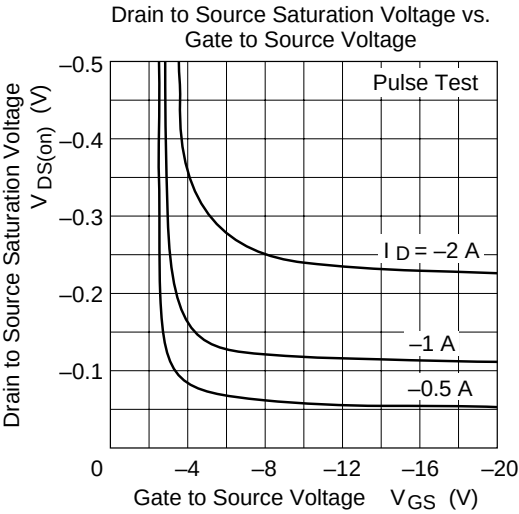
Electrical Characteristics (Ta = 25°C)

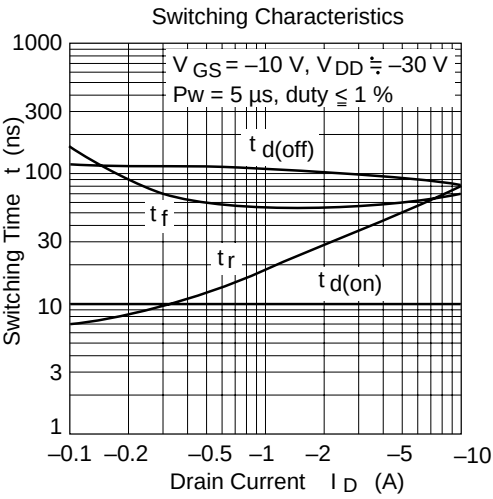
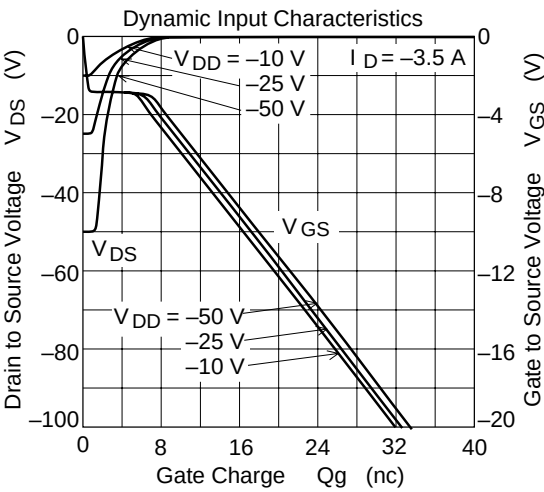
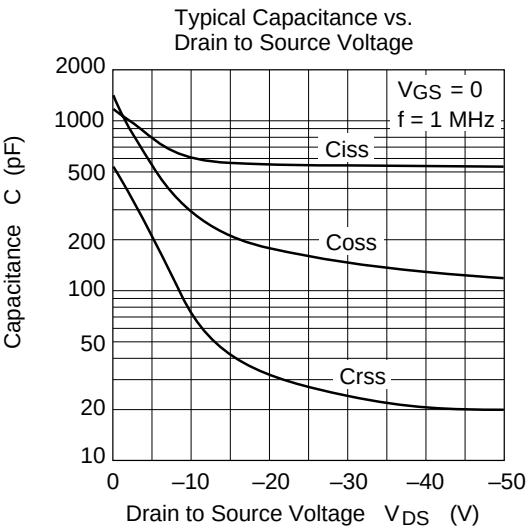
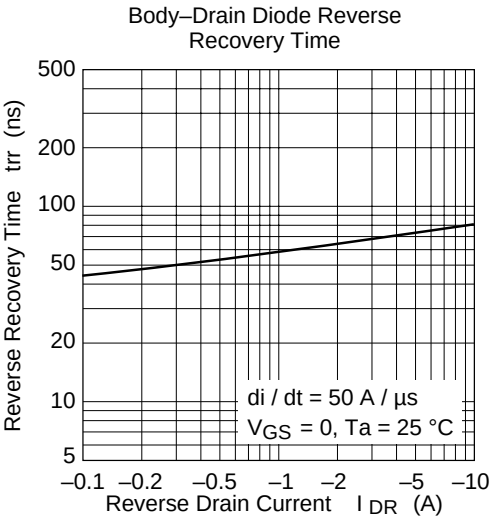
Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage		$V_{(BR)DSS}$	- 60	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage	HAT1038R	I_{DSS}	—	—	- 1	μA	$V_{DS} = -60 \text{ V}$, $V_{GS} = 0$
drain current	HAT1038RJ	I_{DSS}	—	—	- 0.1	μA	
Zero gate voltage	HAT1038R	I_{DSS}	—	—	—	μA	$V_{DS} = -48 \text{ V}$, $V_{GS} = 0$
drain current	HAT1038RJ	I_{DSS}	—	—	-10	μA	Ta=125°C
Gate to source cutoff voltage		$V_{GS(off)}$	- 1.2	—	- 2.2	V	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$
Static drain to source on state		$R_{DS(on)}$	—	0.12	0.15	Ω	$I_D = -2 \text{ A}$, $V_{GS} = -10 \text{ V}$ ^{Note5}
resistance		$R_{DS(on)}$	—	0.16	0.23	Ω	$I_D = -2 \text{ A}$, $V_{GS} = -4 \text{ V}$ ^{Note5}
Forward transfer admittance		$ y_{fs} $	3	4.5	—	S	$I_D = -2 \text{ A}$, $V_{DS} = -10 \text{ V}$ ^{Note5}
Input capacitance		C_{iss}	—	600	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance		C_{oss}	—	290	—	pF	$V_{GS} = 0$
Reverse transfer capacitance		C_{rss}	—	75	—	pF	$f = 1\text{MHz}$
Turn-on delay time		$t_{d(on)}$	—	11	—	ns	$V_{GS} = -10 \text{ V}$, $I_D = -2 \text{ A}$
Rise time		t_r	—	30	—	ns	$V_{DD} \cong -30 \text{ V}$
Turn-off delay time		$t_{d(off)}$	—	100	—	ns	
Fall time		t_f	—	55	—	ns	
Body-drain diode forward voltage		V_{DF}	—	- 0.98	- 1.28	V	$I_F = -3.5 \text{ A}$, $V_{GS} = 0$ ^{Note5}
Body-drain diode reverse recovery time		t_{rr}	—	70	—	ns	$I_F = -3.5 \text{ A}$, $V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

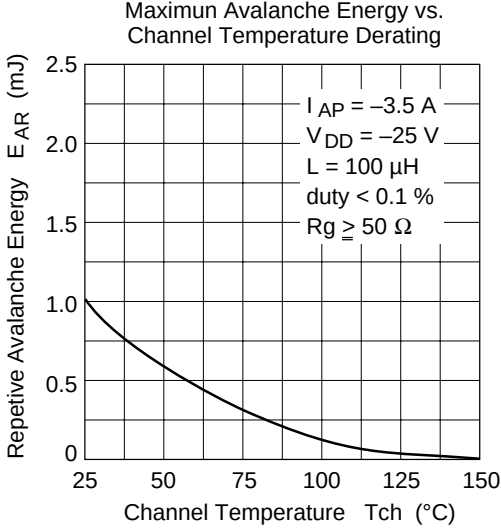
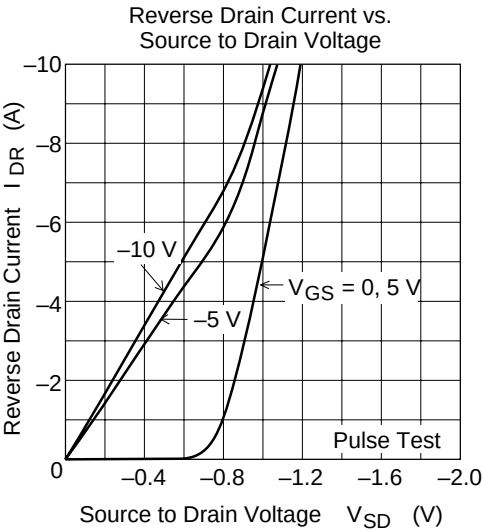
Note: 5. Pulse test

Main Characteristics

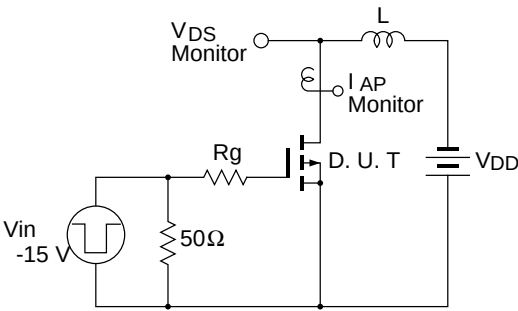






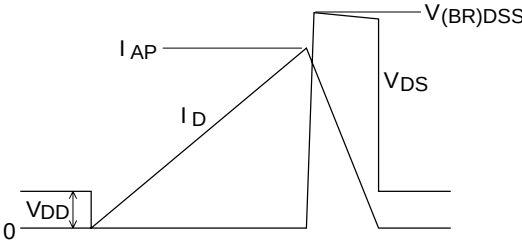


Avalanche Test Circuit

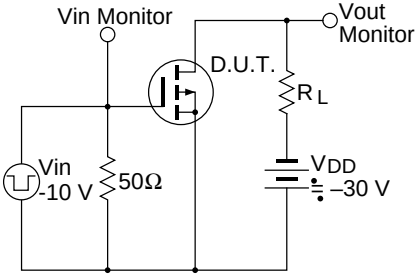


Avalanche Waveform

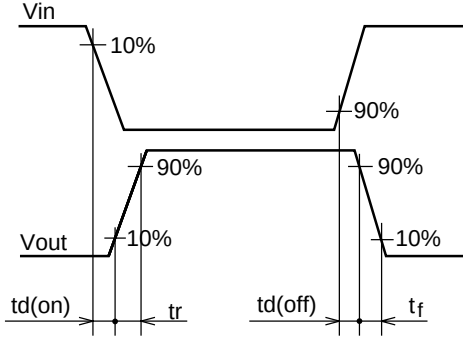
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

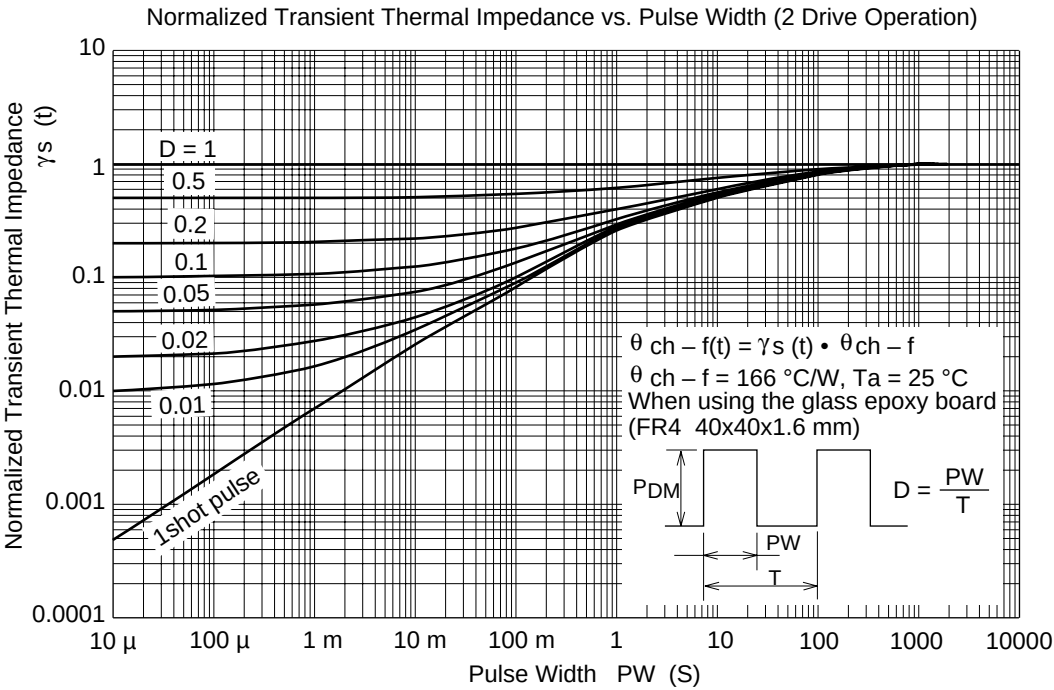
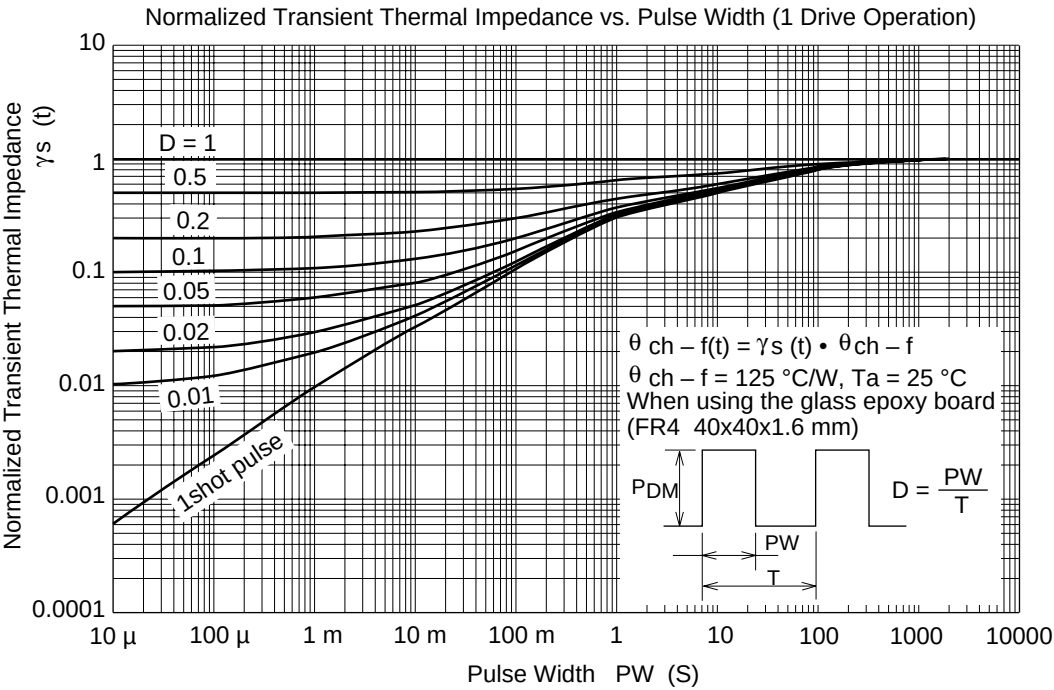


Switching Time Test Circuit



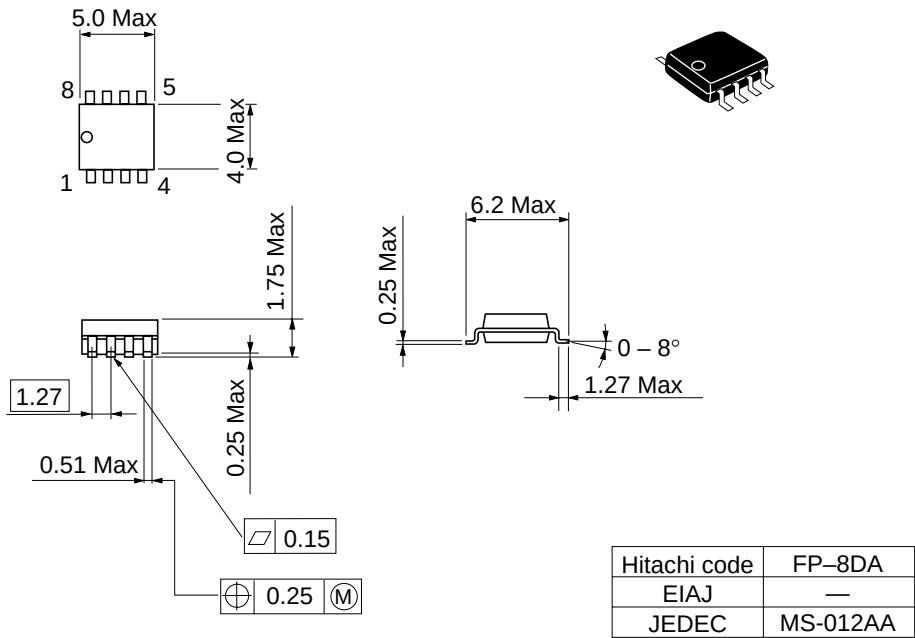
Switching Time Waveform





Package Dimensions

Unit: mm



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